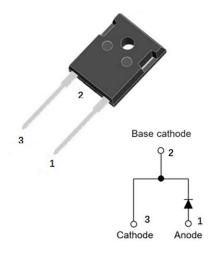
YJD112020NGH



Silicon Carbide Schottky Diode

V _{RRM}	1200V
IF (135°C)	30A
Qc	104nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
 Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-247AC
 Molding compound mosts LIL 04.1(0)
- Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_C =25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112020NGH
Reverse voltage (Repetitive peak) @ Tj=25°C	V _{RRM}	V	1200
Reverse voltage (Surge peak) @ Tj=25°C	V _{RSM}	V	1200
Reverse voltage (DC) @ Tj=25°C	VDC	V	1200
Continuous forward current @ $T_c=25$ °C		A	64
Continuous forward current @ T_c =135°C	IF		30
Continuous forward current @ $T_c=156^{\circ}C$			20
Non-repetitive peak forward surge current @ $T_c=25^{\circ}C$, tp=10ms, Half Sine Wave	I _{FSM}	А	160
Power Dissipation@ Tc=25°C	P	W	300
Power Dissipation@ T _c =110°C	Ртот		130
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	128
Operating junction and Storage temperature range	Tj ,Tstg	°C	-55 to +175

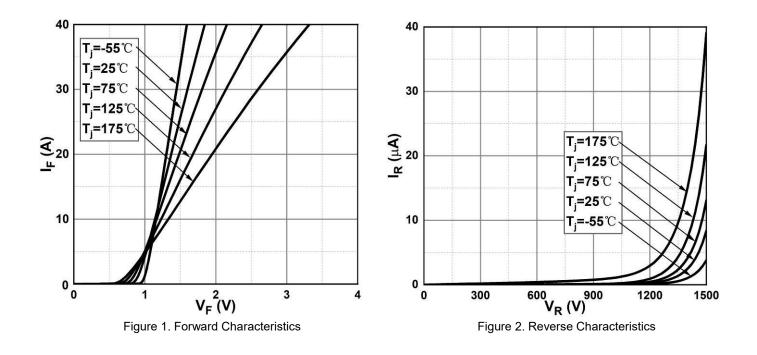
Electrical Characteristics

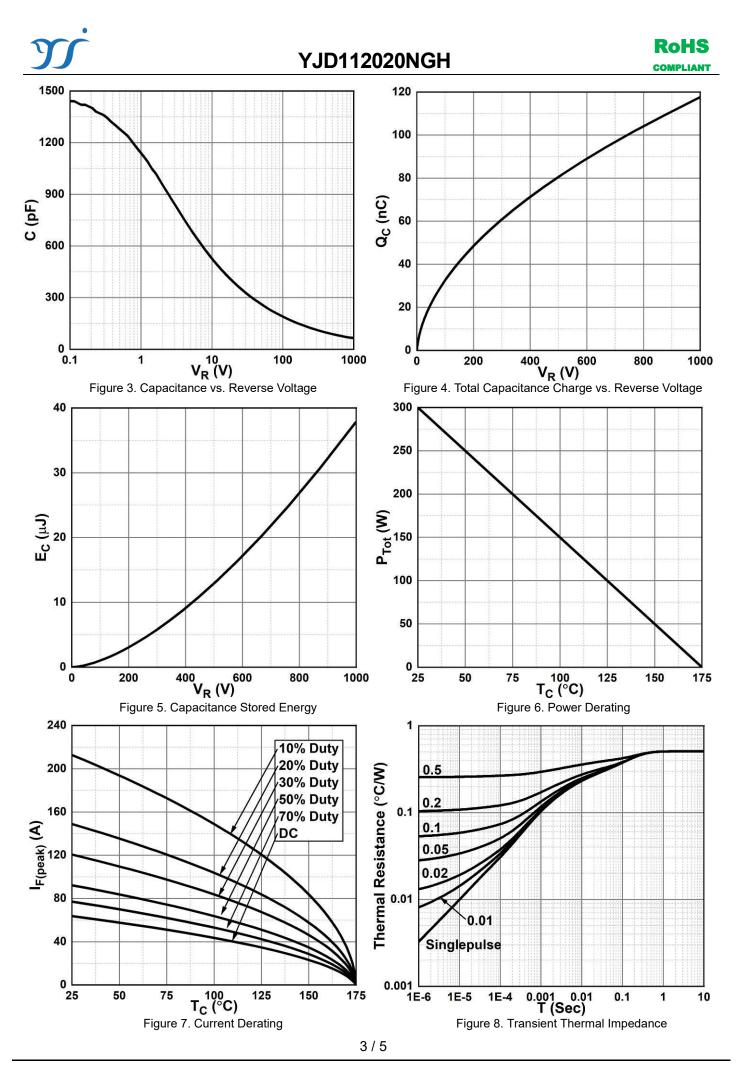
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
E	VF	V	I⊧=20A, Tj=25°C	1.4	1.55
Forward voltage drop			I⊧=20A, Tj=175°C	1.95	-
			V _R =1200V, T _j =25°C	0.5	20
Reverse leakage current	IR	μA	V _R =1200V, T _j =175°C	4	-
Total capacitive charge	Qc	nC	$\begin{array}{l} V_{R}{=}800V,T_{j}{=}25^{\circ}C\ ,\\ Q_{C}{=}{}^{\int_{0}VR}C(V)dV \end{array}$	104	-
		C pF	V _R =0V, f=1MHZ	1509	-
Total capacitance	С		V _R =400V, f=1MHZ	98	-
			V _R =800V, f=1MHZ	70	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	27	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{_{ ext{ hetaJ-C}}}$	°C/W	0.5

■Typical Characteristics



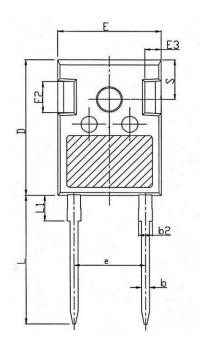


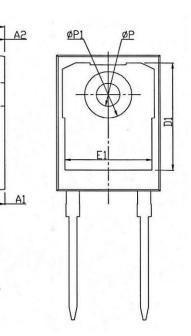
Yangzhou Yangjie Electronic Technology Co., Ltd.



Outline Dimensions

TO-247AC





TO-247AC				
Dim	Min	Max		
А	4.80	5.20		
A1	2.21	2.61		
A2	1.85	2.15		
b	1.11	1.36		
b2	1.91	2.21		
С	0.51	0.75		
D	20.70	21.30		
D1	16.25	16.85		
E	15.50	16.10		
E1	13.00	13.60		
E2	4.80	5.20		
E3	2.30	2.70		
е	10.88BSC			
L	19.62	20.22		
L1	-	4.30		
ΦP	3.40	3.80		
Φ P 1	-	7.30		
S	6.15BSC			





Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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